

Low momentum PID at High B-field

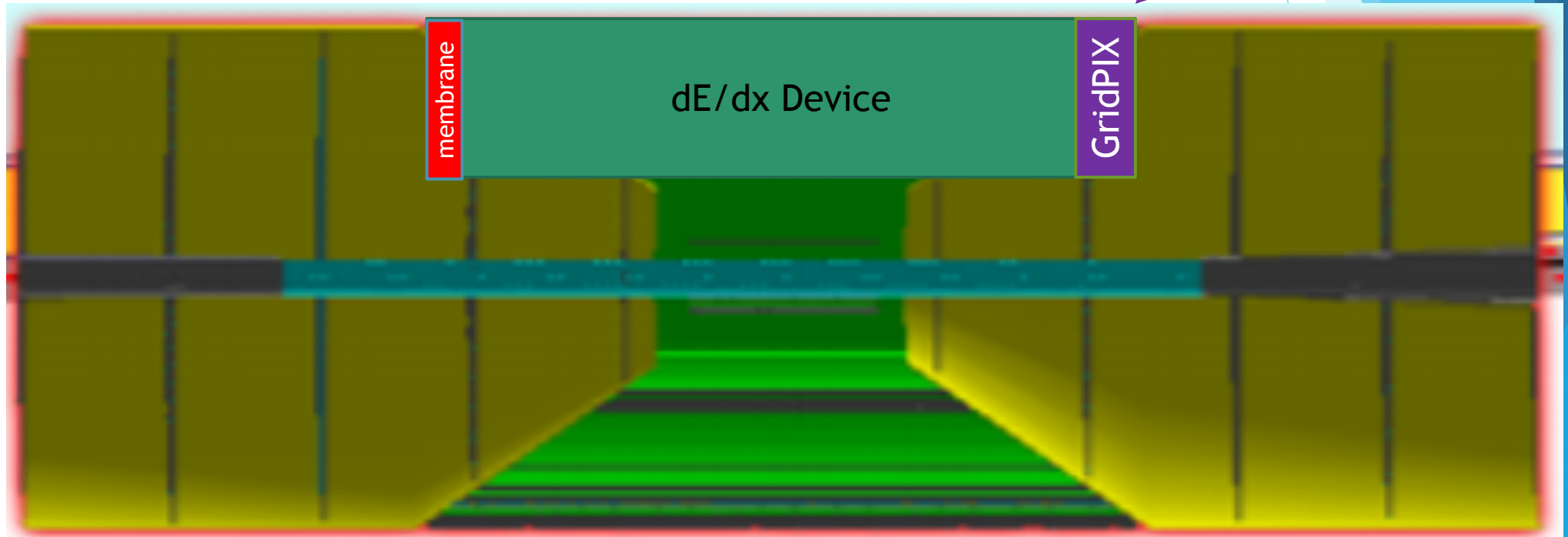
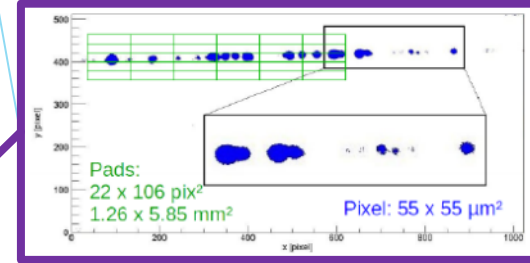
("Mostly Silicon" Tracker with a PID layer)

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- GridPix is a 55 μm \times 55 μm pixel readout for a gaseous TPC
- First Timepix3 based GridPix test beam (2017)
- Quad module performance from test beam (2018)
- Investigations of the 8 quad detector (2020)

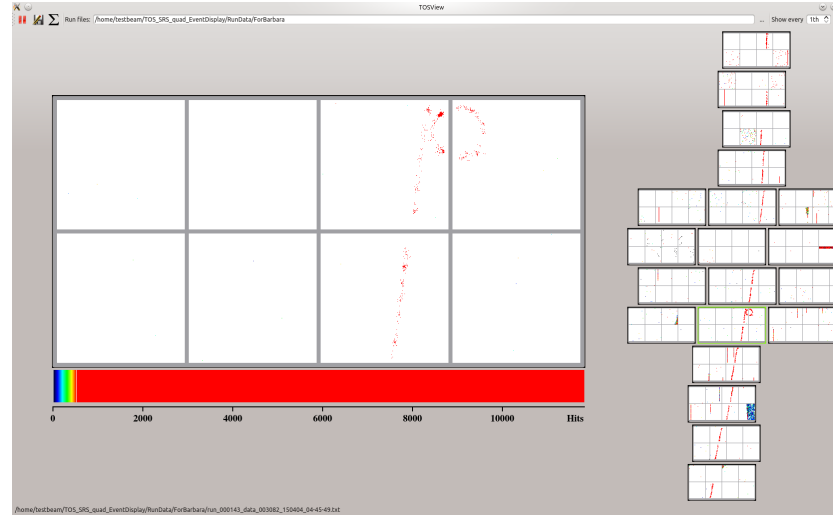
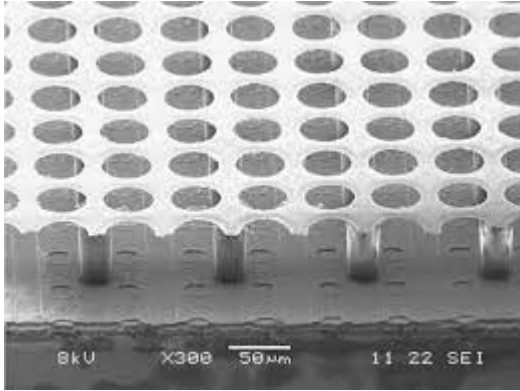
Low Momentum PID

- ▶ High magnetic field curls low(er) momentum particles.
 - ▶ Option #1: We don't care about them. (bad option)
 - ▶ Option #2: Lower the B-field for "special runs". (poor option)
 - ▶ Option #3: PID on these particles BEFORE they curl up.



Mostly ~~—~~ All-Si Tracker

GridPIX Overview



▶ Ultimate dE/dx device.

- ▶ Avalanche grid in front of $55 \times 55 \mu\text{m}^2$ pixels.
- ▶ >90% efficiency for single electrons (Polya NOT exponential).
- ▶ Goal:
 - ▶ Enough diffusion to get every electron into a different hole.
 - ▶ Count electrons one-by-one.
- ▶ Three generations of development and continuing.

▶ Large area is VERY expensive, but this proposal is small area.

- ▶ Careful: ~3kW of power must be removed.

3D e-by-e tracking

Observed standard deviation	41 μm
Statistical errors	25 μm
Systematic errors in the pixel plane and drift direction	19 μm
Multiple scattering	22 μm
Unidentified systematic error	14 μm

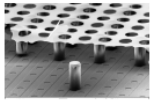
Pros:

- Known/Proven Technology
- Active further development (Bonn)
- Best $\frac{dE}{dx}$ possible (~count each electron)
- Affordable for a small area
- High resolution tracking
 - Also loves outer MPGDs!
- Low mass in electron arm
- Continuous (aka streaming) readout

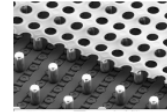
Cons:

- 3 kW of power.
- Must find a low pass way to handle.
- Services “bulky” (compared to just Si)
 - Gas
 - HV membrane
 - Cooling
 - DC power lines (3kV goes in too)

A Little Geometry

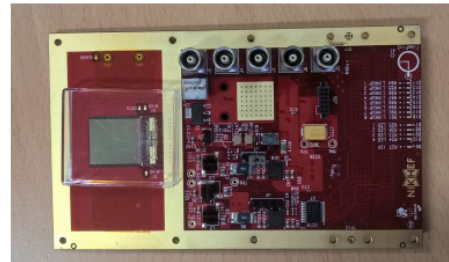
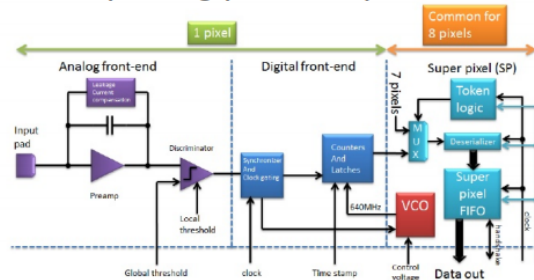
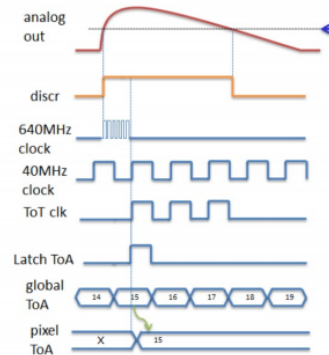


Timepix3



Timepix3 → Timepix4

- Number of pixels: 256 × 256 pixels
 - Pixel pitch: 55 × 55 μm²
 - ENC: ~ 60 e⁻
 - Charge (ToT) and time (ToA) available for each hit
 - Timing resolution: 1.56 ns for duration of ~410 μs
 - Zero suppression on chip (sparse readout)
 - Multi-hit capable (pixels sensitive after t_{ToT} + 475 ns)
- Super-pixels store hits for some time
- Output rate up to 5.12 Gbps
 - Power pulsing possible (800 ns for start up)



		Timepix3 (2013)	Timepix4 (2019)	
Technology		130nm – 8 metal	65nm – 10 metal	
Pixel Size		55 x 55 μm	55 x 55 μm	
Pixel arrangement		3-side buttable 256 x 256	4-side buttable 512 x 448 3.5x	
Sensitive area		1.98 cm ²	6.94 cm²	
Readout Modes	Data driven (Tracking)	Mode	TOT and TOA	
		Event Packet	48-bit	64-bit 33%
		Max rate	0.43x10 ⁶ hits/mm ² /s	3.58x10⁶ hits/mm²/s
	Frame based (Imaging)	Max Pix rate	1.3 KHz/pixel	10.8 KHz/pixel 8x
		Mode	PC (10-bit) and iTOT (14-bit)	CRW: PC (8 or 16-bit)
		Frame	Zero-suppressed (with pixel addr)	Full Frame (without pixel addr)
	Max count rate	~0.82 x 10 ⁹ hits/mm ² /s	~5 x 10 ⁹ hits/mm ² /s 5x	
TOT energy resolution		< 2KeV	< 1Kev 2x	
TOA binning resolution		1.56ns	195ps 8x	
TOA dynamic range		409.6 μs (14-bits @ 40MHz)	1.6384 ms (16-bits @ 40MHz) 4x	
Readout bandwidth		≤5.12Gb (8x SLVS@640 Mbps)	≤163.84 Gbps (16x @10.24 Gbps) 2x	
Target global minimum threshold		<500 e ⁻	<500 e ⁻	



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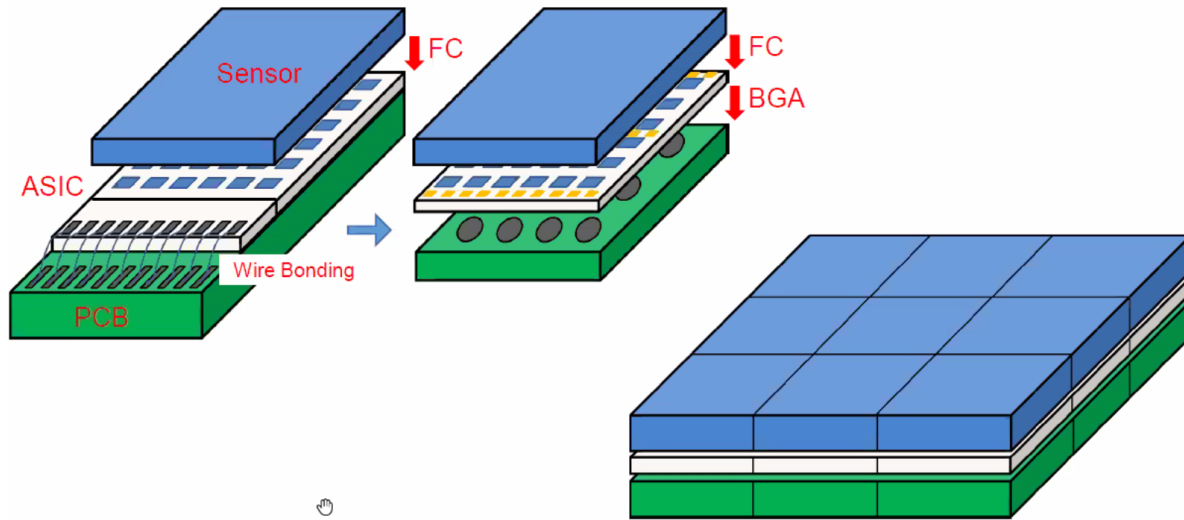
- ▶ 55 μm × 256 = 1.4 cm active area.
- ▶ 100cm/1.4cm = 71.4...call it 72 chips x 72 chips (but must eliminate holes)

Rough number of actual chips: $\frac{\pi(50^2 - 25^2)}{1.4^2} = 3,005 \text{ chips}$ $\frac{\pi(50^2 - 20^2)}{1.4^2} = 3,366 \text{ chips}$

TimePIX4 is more Promising for EIC



4-side buttable pixel arrangement

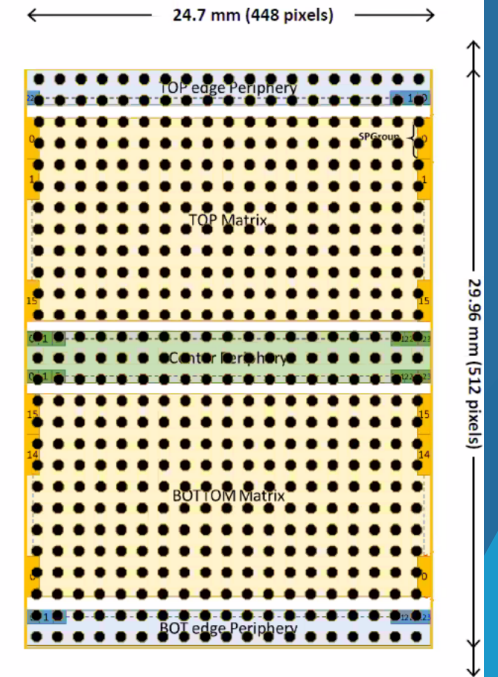


- Target to build **large area detectors** by combining smaller modules
- The through-silicon vias (TSVs) is the key technology for this paradigm shift



Timepix4 floorplan arrangement

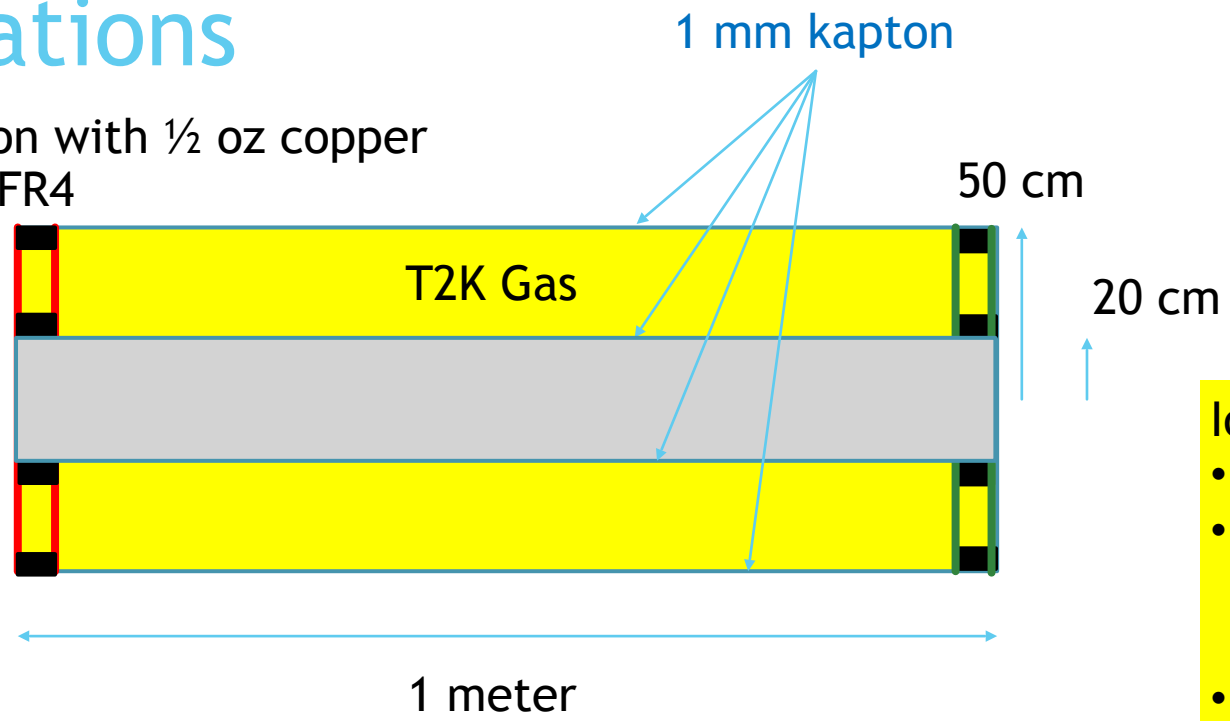
- 512 x 448 of 55 x 55 μm pixels
- 3 “hidden” peripheries with TSV (Through-Silicon-Vias):
 - TOP Edge: Data Readout & Slow Control
 - 147 TSVs/WBs: 106 POWER/GND and 41 IO
 - BOTTOM Edge: Data Readout & Slow Control:
 - 147 TSVs/WBs: 106 POWER/GND and 41 IO
 - CENTER: Slow Control and Analog Blocks (DACs, ADC, Band-Gaps...)
 - 147 TSVs: 124 POWER/GND and 23 IO
- On-chip bump to pixel redistribution layer (RDL)
- Chip size:
 - With WB (wirebonds extenders): 29.96 mm x 24.7 mm
 - >93.7% active area (28.16mm x 24.64mm)
 - Without WB (TSV Only): 28.72 mm x 24.7 mm
 - >99.5% active area (28.16mm x 24.64mm)
- Control architecture allows to operated Timepix4 from any of the 3 peripheries:
 - i2C protocol
 - Custom Slow Control protocol
 - Interface to DAQ:
 - Through 3xTSVs
 - Through 2xWB
- Fast readout requires at least 1 serial link enabled in each edge periphery:
 - Serial links are highly configurable 40MBps \rightarrow 10GBps



- ▶ Model 4 replaces wires bond with bump bond (improves active area).
- ▶ 93.7% \rightarrow 99.5% active area.
- ▶ DAQ interface by Through-Silicon-Vias (TSV).

First Simulations

- 5 mil Kapton with ½ oz copper
- 0.063 inch FR4

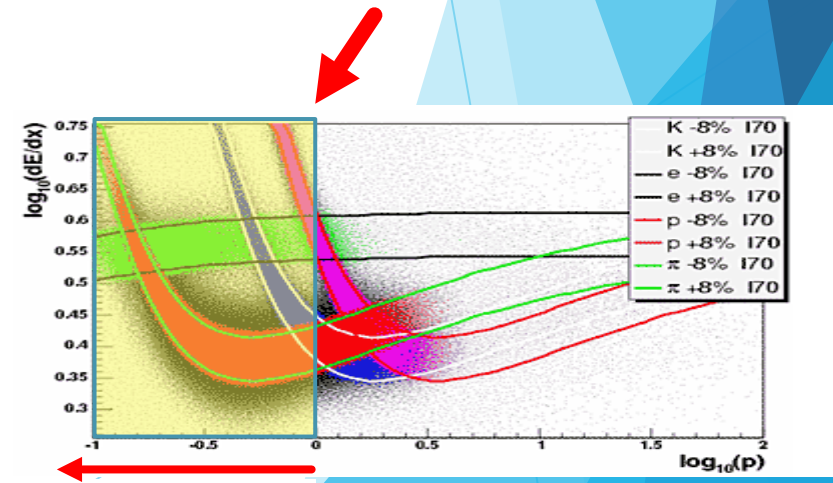


Ionization Stats:

- 95% Ar approx. as 100% Ar
- Avg: 23 primary/cm; 94 total/cm
 - Best case dE/dx ~4%
 - Worst case: dE/dx ~7%
- NOTE:
 - Life is easy at low p

■ 2cm x 2cm C-fiber box with 2 mm walls (Hollow)

- ▶ A starting Geometry.
- ▶ Primary ionization from Garfield
- ▶ GridPIX response from Jochen, Michael Lupberger (RD51)
- ▶ Geometry from Sanghwa
- ▶ Parallel Efforts
 - ▶ Standalone and GEANT - made correct



Less than 1 GeV/c